

MS23N36

P-Channel 30-V (D-S) MOSFET

Description

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

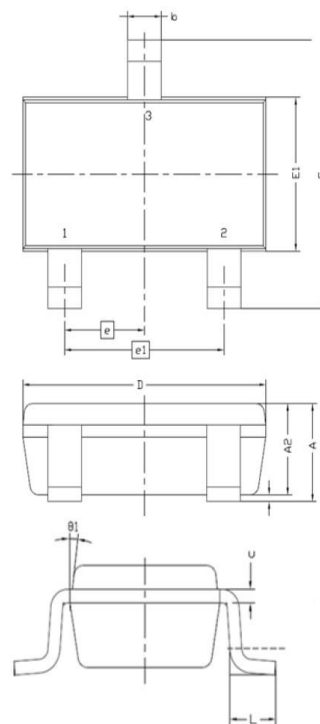
Features

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Miniature SOT-23 Surface Mount Package
- Saves Board Space
- RoHS compliant package

Package type : SOT-23

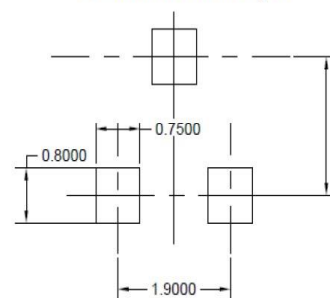
Packing & Order Information

3,000/Reel



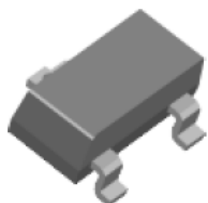
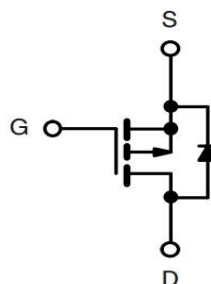
Symbol	MILLIMETERS	
	MIN	MAX
A	0.8	1.2
A1	0	0.1
A2	0.7	1.1
b	0.3	0.5
c	0.1	0.2
D	2.7	3.1
E	2.6	3
E1	1.4	1.8
e	0.95 BSC	
e1	1.9 BSC	
L	0.3	0.6
θ1	7° NOM	

Recommended Pad Layout



Note: Drain opening is recommended to be solder mask defined in a copper fill for improved thermal performance

Graphic symbol



**RoHS
COMPLIANT**

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current ^a ($T_A=25^\circ\text{C}$)	5.2	A
	Continuous Drain Current _a ($T_A=70^\circ\text{C}$)	4.1	A
I_{DM}	Pulsed Drain Current ^b	30	A
I_S	Continuous Source Current (Diode Conduction) ^a	1.6	A
P_D	Power Dissipation ^a ($T_A=25^\circ\text{C}$)	1.3	W
	Power Dissipation ^a ($T_A=70^\circ\text{C}$)	0.8	W
T_J/T_{STG}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

- Drain current limited by maximum junction temperature

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Thermal Resistance Ratings

Symbol	Parameter	Maximum	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ^a ($t \leq 5$ sec)	100	°C/W
	Maximum Junction-to-Ambient ^a (Steady-State)	166	

Notes :

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

Static

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$V_{GS(th)}$	Gate-Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	0.6			V
I_{GSS}	Gate-Body Leakage	$V_{DS} = 0$ V, $V_{GS} = 8$ V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24$ V, $V_{GS} = 0$ V $V_{DS} = 24$ V, $V_{GS} = 0$ V, $T_J = 55^\circ C$			1 25	uA
$I_{D(on)}$	On-State Drain Current ^A	$V_{DS} = 5$ V, $V_{GS} = 4.5$ V	20			A
$R_{DS(on)}$	Drain-Source On-Resistance ^A	$V_{GS} = 4.5$ V, $I_D = 5.2$ A $V_{GS} = 2.5$ V, $I_D = 3.7$ A			32 64	mΩ
g_{fs}	Forward Transconductance ^A	$V_{DS} = 15$ V, $I_D = 5.2$ A		40		S
V_{SD}	Diode Forward Voltage	$I_S = 2.3$ V, $V_{GS} = 0$ V		0.7		V

Dynamic^b

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
Q_g	Total Gate Charge	$V_{DS} = 15$ V, $I_D = 4.5$ A, $V_{GS} = 5.2$ V		6.0		nC
Q_{gs}	Gate-Source Charge			1.0		nC
Q_{gd}	Gate-Drain Charge			1.5		nC
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 25$ V, $R_L = 25$ Ω, $V_{GEN} = 10$ V, $I_D = 1$ A		7.8		ns
t_r	Rise Time			5.2		ns
$t_{d(off)}$	Turn-Off Delay Time			31.2		ns
t_f	Fall Time			8		ns

Notes :

- Pulse test: PW $\leq 300\mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

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Characteristic Curves

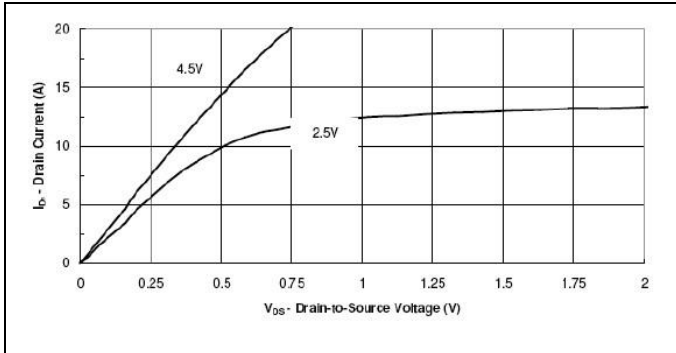


FIG.1-OUTPUT CHARACTERISTICS

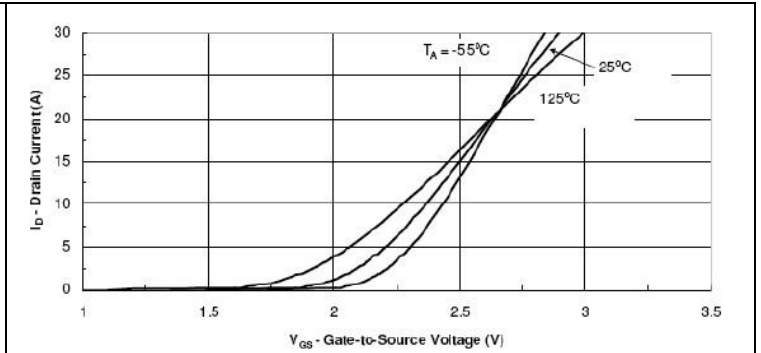


FIG.2-TRANSFER CHARACTERISTICS

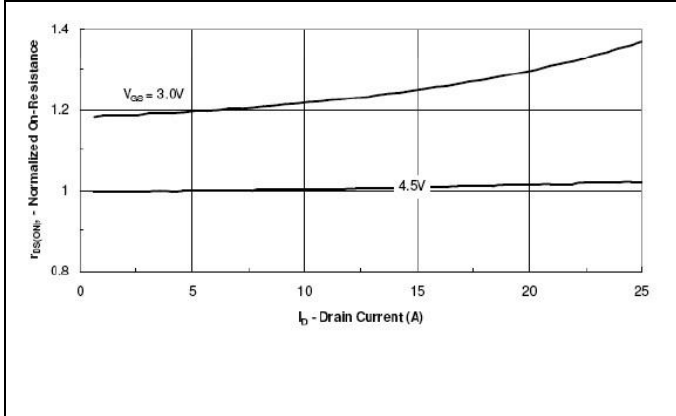


FIG.3-ON-RESISTANCE VS DRAIN CURRENT

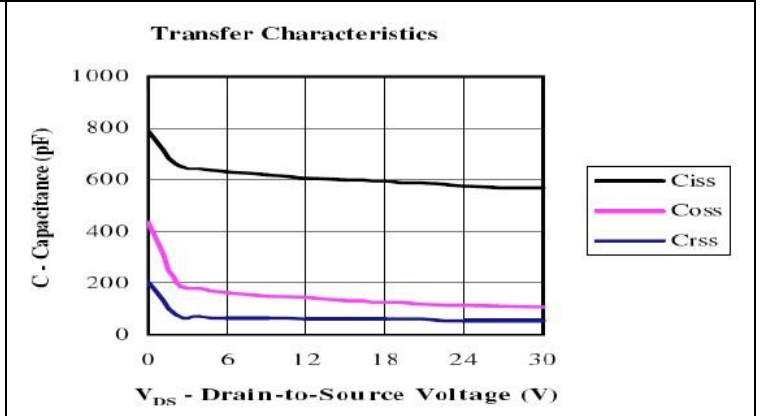


FIG.4-CAPACITANCE

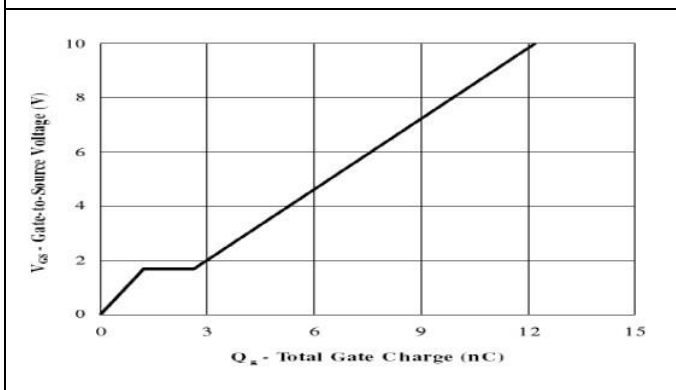


FIG.5-GATE CHARGE

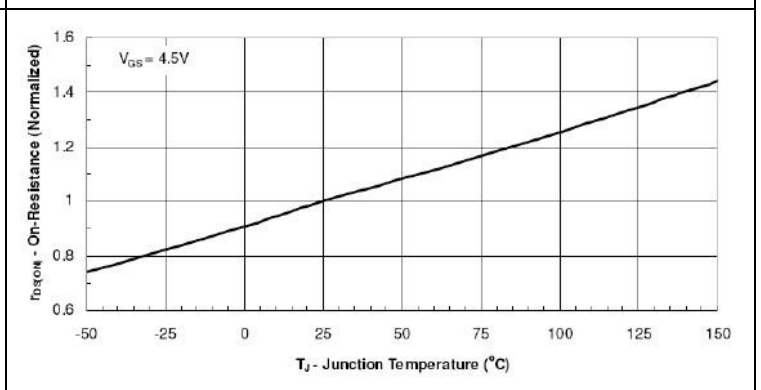


FIG.6-ON-RESISTANCE VS. JUNCTION TEMPERATURE

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Characteristic Curves

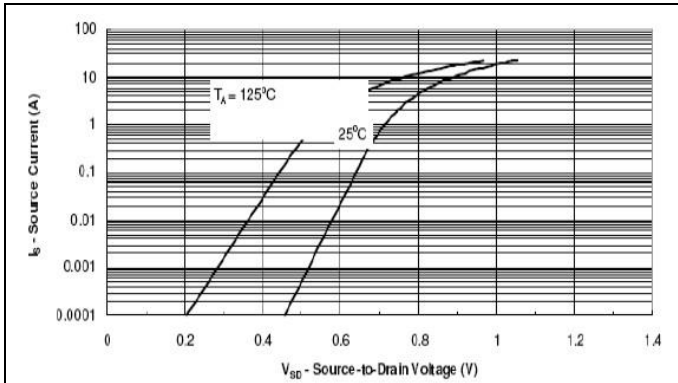


FIG. 7-SOURCE-DRAIN DIODE FORWARD VOLTAGE

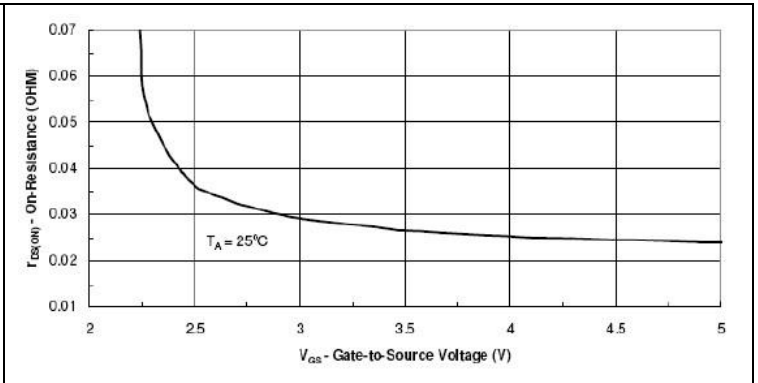


FIG. 8-ON-RESISTANCE VS. GATE-TO SOURCE VOLTAGE

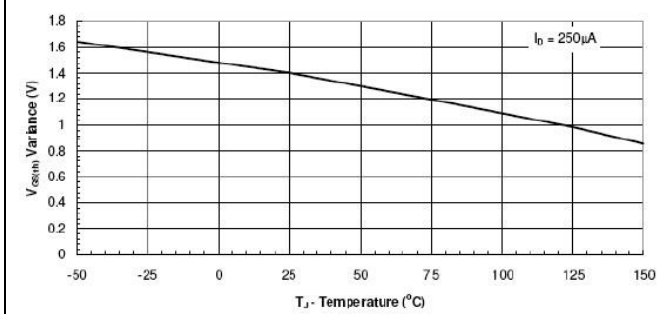


FIG. 9-THRESHOLD VOLTAGE

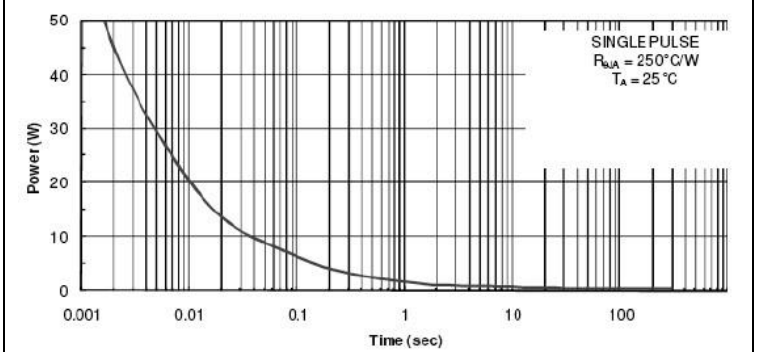


FIG. 10-SINGLE PULSE POWER

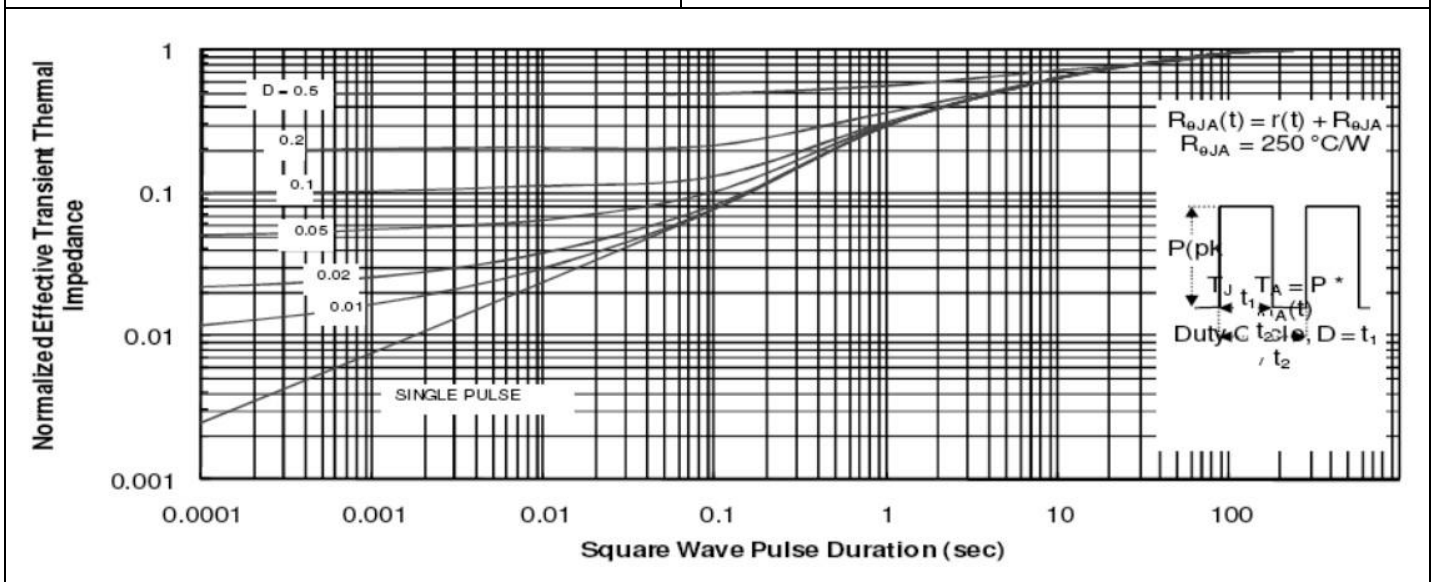


FIG. 11-NORMALIZED THERSIENT IMPEDANCE, JUNCTION-TO-AMBIENT

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